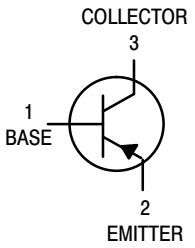
PNP General Purpose Transistor

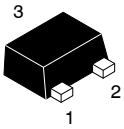
MMBT2907AM3T5G

The MMBT2907AM3T5G device is a spin−off of our popular SOT−23 three−leaded device. It is designed for general purpose amplifier applications and is housed in the SOT−723 surface mount package. This device is ideal for low−power surface mount applications where board space is at a premium.



Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant



SOT−723
CASE 631AA
STYLE 1

MARKING DIAGRAM

AC = Specific Device Code
M = Date Code

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−60	Vdc
Collector − Base Voltage	V_{CBO}	−60	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	 265 2.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	640 5.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2907AM3T5G	SOT−723 (Pb−Free)	8000/Tape & Reel
NSVMMBT2907AM3T5G	SOT−723 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 3) (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−60	–	Vdc
Collector−Base Breakdown Voltage (I_C = −10 μAdc, I_E = 0)	$V_{(BR)CBO}$	−60	–	Vdc
Emitter−Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	–	Vdc
Collector Cutoff Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)	I_{CEX}	–	−50	nAdc
Collector Cutoff Current (V_{CB} = −50 Vdc, I_E = 0) (V_{CB} = −50 Vdc, I_E = 0, T_A = 125°C)	I_{CBO}	– –	−0.010 −10	μAdc
Base Cutoff Current (V_{CE} = −30 Vdc, $V_{EB(off)}$ = −0.5 Vdc)	I_{BL}	–	−50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = −0.1 mAdc, V_{CE} = −10 Vdc) (I_C = −1.0 mAdc, V_{CE} = −10 Vdc) (I_C = −10 mAdc, V_{CE} = −10 Vdc) (I_C = −150 mAdc, V_{CE} = −10 Vdc) (I_C = −500 mAdc, V_{CE} = −10 Vdc) (Note 3)	h_{FE}	 75 100 100 100 50	 - - - 300 -	-
Collector−Emitter Saturation Voltage (Note 3) (I_C = −150 mAdc, I_B = −15 mAdc) (Note 3) (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{CE(sat)}$	 - -	 −0.4 −1.6	Vdc
Base−Emitter Saturation Voltage (Note 3) (I_C = −150 mAdc, I_B = −15 mAdc) (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{BE(sat)}$	 - -	 −1.3 −2.6	Vdc
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain − Bandwidth Product (Notes 3, 4) (I_C = −50 mAdc, V_{CE} = −20 Vdc, f = 100 MHz)	f_T	200	–	MHz
Output Capacitance (V_{CB} = −10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	8.0	pF
Input Capacitance (V_{EB} = −2.0 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	–	30	
SWITCHING CHARACTERISTICS				
Turn−On Time	(V_{CC} = −30 Vdc, I_C = −150 mAdc, I_{B1} = −15 mAdc)	t_{on}	–	45	ns
Delay Time		t_d	–	10	
Rise Time		t_r	–	40	
Turn−Off Time	(V_{CC} = −6.0 Vdc, I_C = −150 mAdc, I_{B1} = I_{B2} = −15 mAdc)	t_{off}	–	100	
Storage Time		t_s	–	80	
Fall Time		t_f	–	30	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

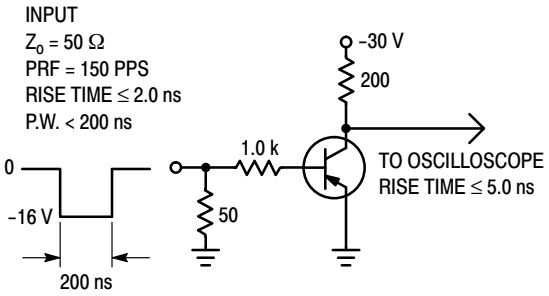


Figure 1. Delay and Rise Time Test Circuit

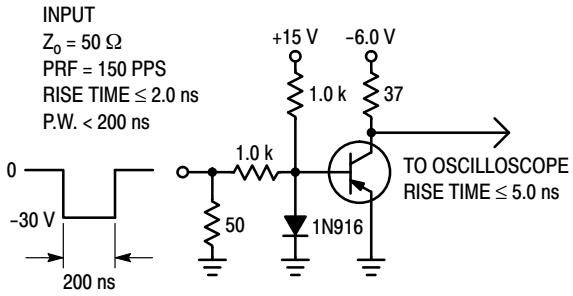


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

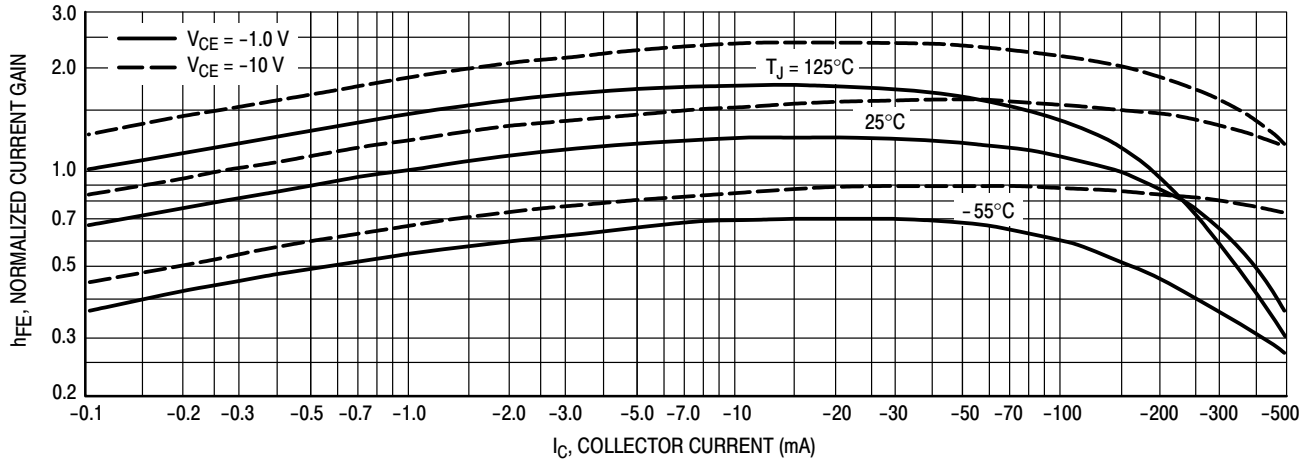


Figure 3. DC Current Gain

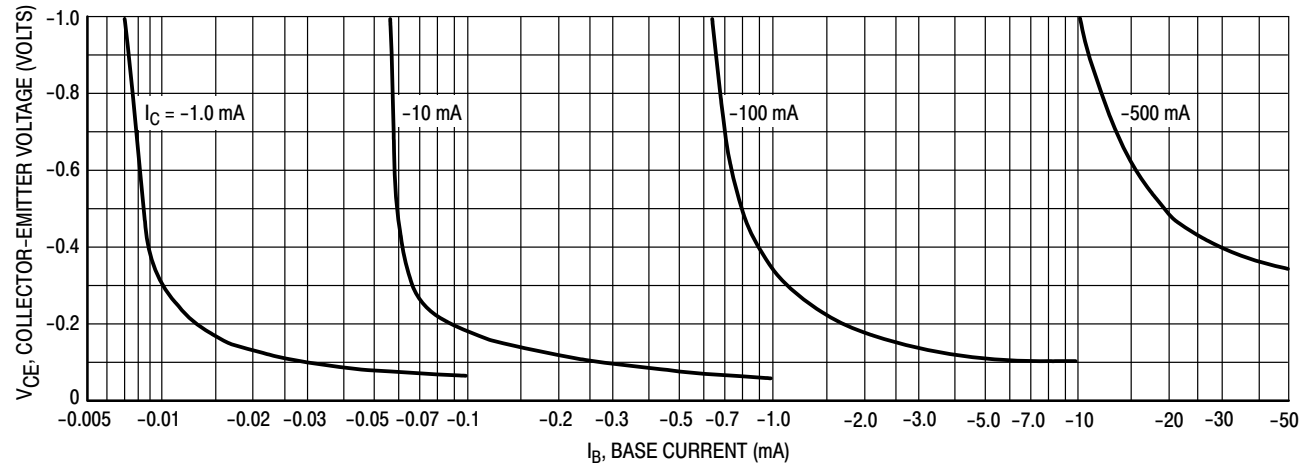


Figure 4. Collector Saturation Region

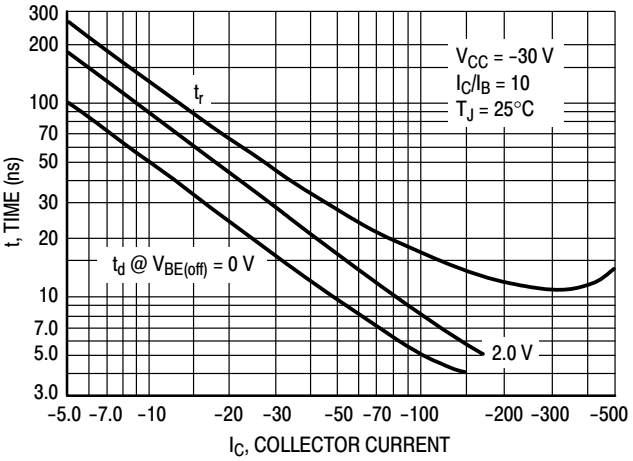


Figure 5. Turn−On Time

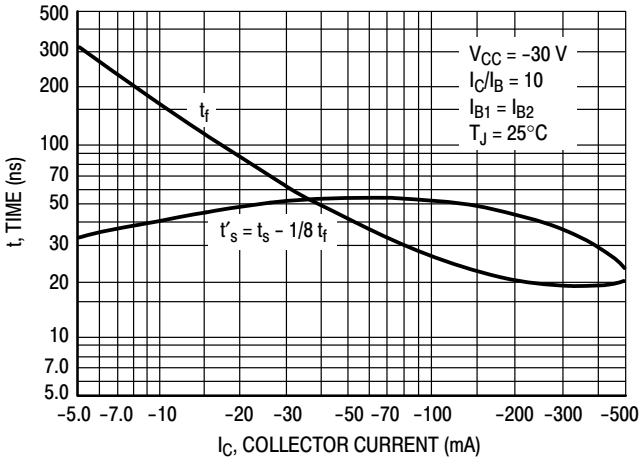


Figure 6. Turn−Off Time

TYPICAL SMALL−SIGNAL Characteristics

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

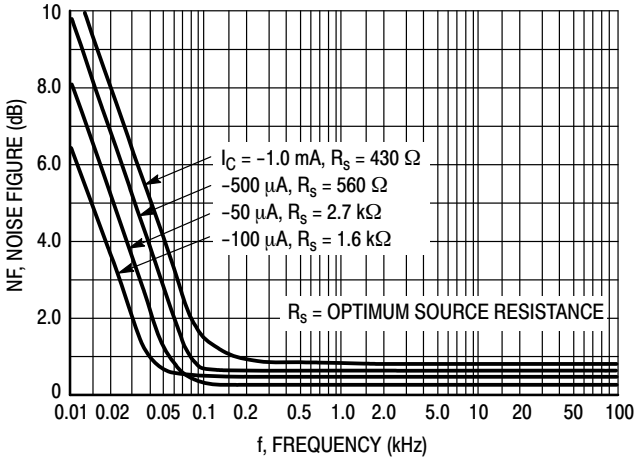


Figure 7. Frequency Effects

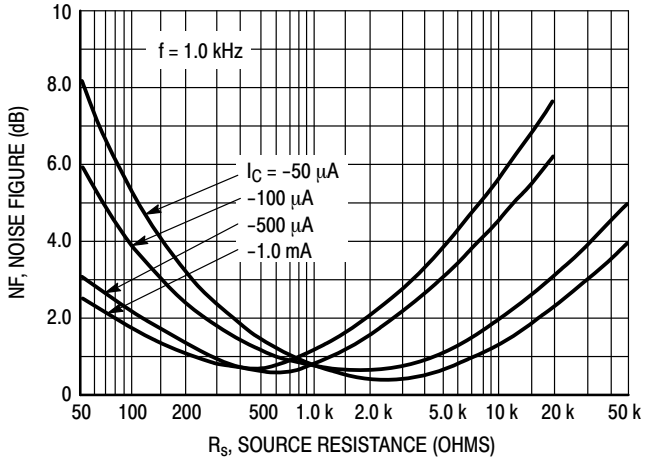


Figure 8. Source Resistance Effects

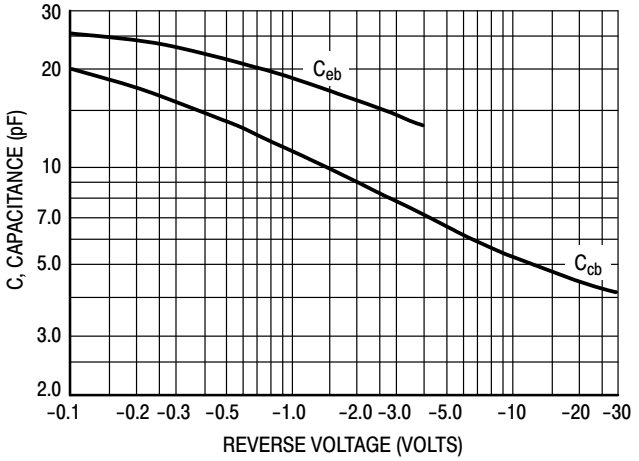


Figure 9. Capacitances

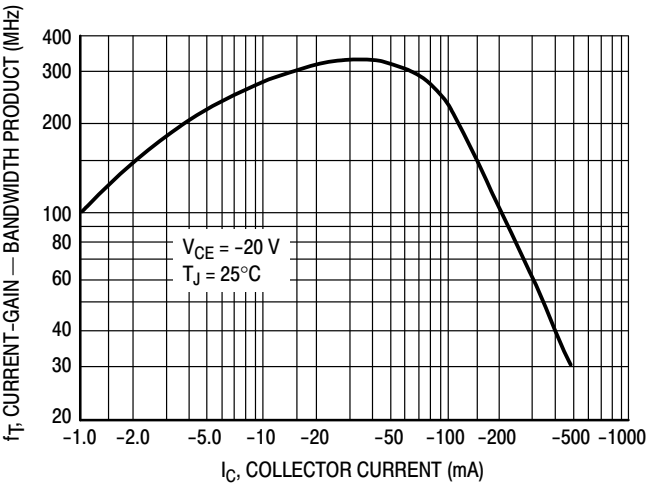


Figure 10. Current−Gain − Bandwidth Product

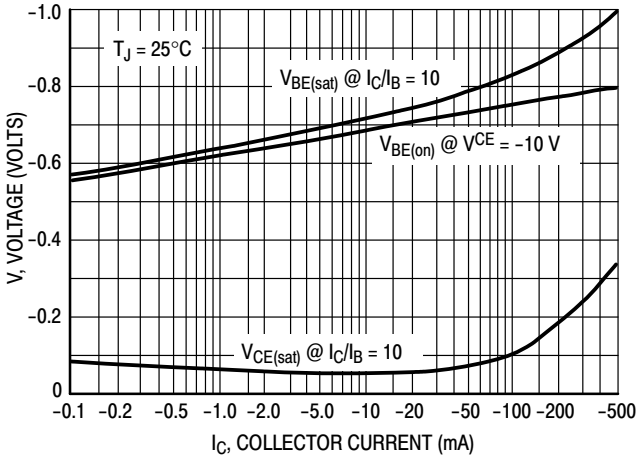


Figure 11. “On” Voltage

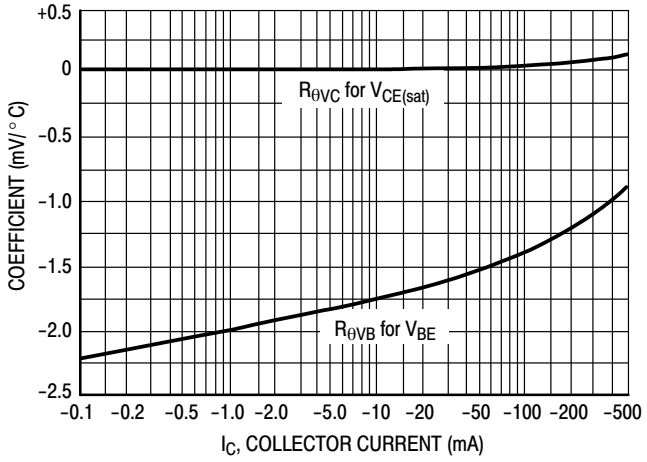
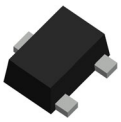


Figure 12. Temperature Coefficients

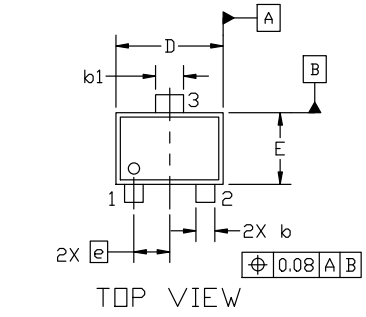


SOT−723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

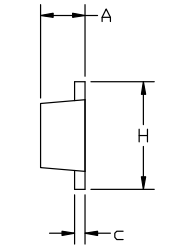
DATE 24 JAN 2024

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

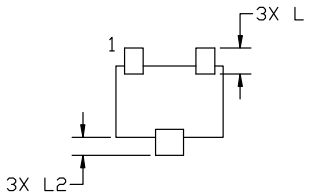
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



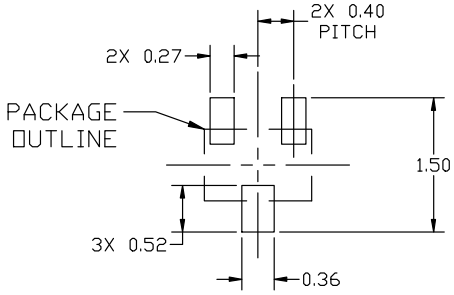
TOP VIEW



SIDE VIEW



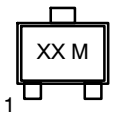
BOTTOM VIEW



RECOMMENDED MOUNTING
FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

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DESCRIPTION:	**SOT−723 1.20x0.80x0.50, 0.40P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

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